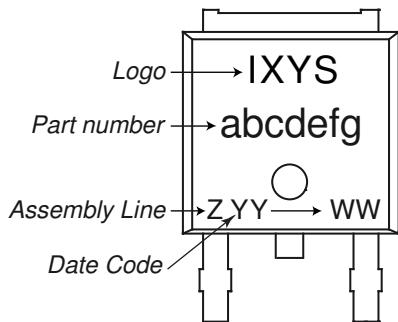


Schottky			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			150	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			150	V
I_R	reverse current, drain current	$V_R = 150 V$ $V_R = 150 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		250 2.5	μA mA
V_F	forward voltage drop	$I_F = 6 A$ $I_F = 12 A$ $I_F = 6 A$ $I_F = 12 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		0.78 0.86 0.62 0.71	V V V V
I_{FAV}	average forward current	$T_C = 165^\circ C$ rectangular $d = 0.5$	$T_{VJ} = 175^\circ C$		6	A
V_{F0} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 175^\circ C$		0.45 14.6	V $m\Omega$
R_{thJC}	thermal resistance junction to case				3	K/W
R_{thCH}	thermal resistance case to heatsink			0.50		K/W
P_{tot}	total power dissipation	$T_C = 25^\circ C$			50	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}; V_R = 0 V$	$T_{VJ} = 45^\circ C$		120	A
C_J	junction capacitance	$V_R = 24 V$ f = 1 MHz	$T_{VJ} = 25^\circ C$		82	pF

Package TO-252 (DPak)

Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	<i>RMS current</i>	per terminal ¹⁾			20	A
T_{VJ}	<i>virtual junction temperature</i>		-55		175	°C
T_{op}	<i>operation temperature</i>		-55		150	°C
T_{stg}	<i>storage temperature</i>		-55		150	°C
Weight				0.3		g
F_c	<i>mounting force with clip</i>		20		60	N

¹⁾ I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

Product Marking

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSS6-015AS	6Y150AS	Tape & Reel	2500	498912

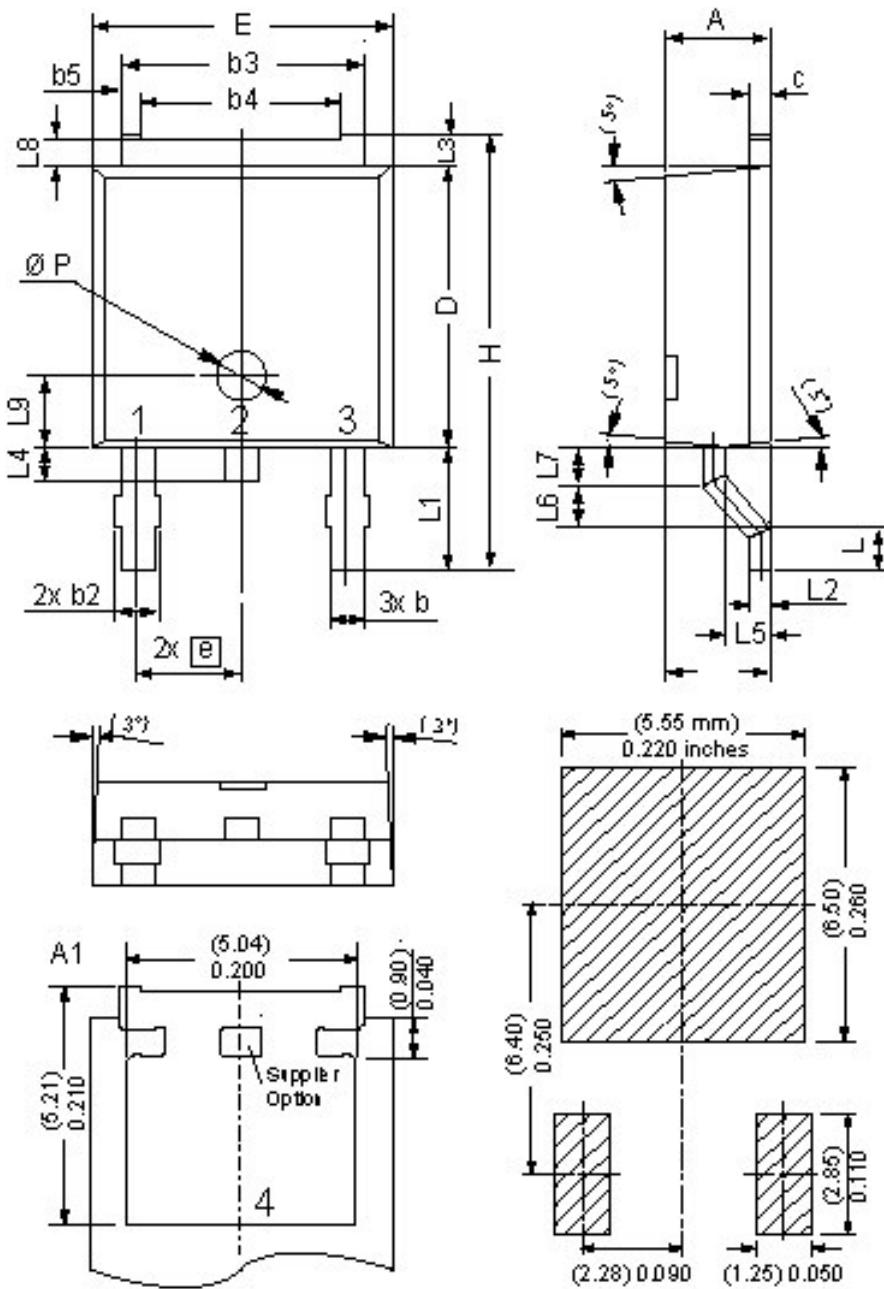
Equivalent Circuits for Simulation** on die level* $T_{VJ} = 175 \text{ }^{\circ}\text{C}$

	Schottky
V_0	R_0
$V_{0\max}$	threshold voltage
$R_{0\max}$	slope resistance *

V

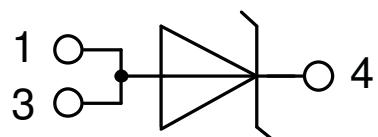
mΩ

Outlines TO-252 (DPak)



Dim.	Millimeters		Inches	
	min	max	min	max
A	2.20	2.40	0.087	0.094
A1	2.10	2.50	0.083	0.098
b	0.66	0.86	0.026	0.034
b2	-	0.96	-	0.038
b3	5.04	5.64	0.198	0.222
b4	4.34 BSC	4.34 BSC	0.171 BSC	0.171 BSC
b5	0.50 BSC	0.50 BSC	0.020 BSC	0.020 BSC
c	0.40	0.86	0.016	0.034
D	5.90	6.30	0.232	0.248
E	6.40	6.80	0.252	0.268
e	2.10	2.50	0.083	0.098
H	9.20	10.10	0.362	0.398
L	0.55	1.28	0.022	0.050
L1	2.50	2.90	0.098	0.114
L2	0.40	0.60	0.016	0.024
L3	0.50	0.90	0.020	0.035
L4	0.60	1.00	0.024	0.039
L5	0.82	1.22	0.032	0.048
L6	0.79	0.99	0.031	0.039
L7	0.81	1.01	0.032	0.040
L8	0.40	0.80	0.016	0.031
L9	1.50 BSC	1.50 BSC	0.059 BSC	0.059 BSC
Ø P	1.00 BSC	1.00 BSC	0.039 BSC	0.039 BSC

Recommended
min. foot print



Schottky

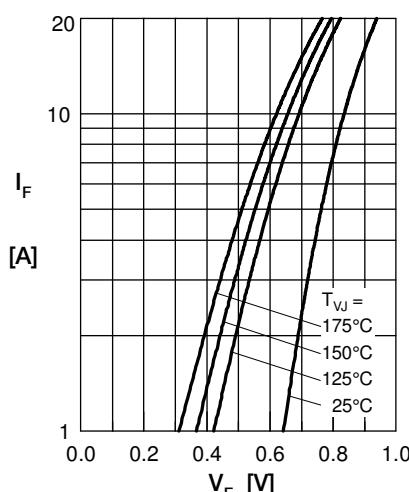


Fig. 1 Max. forward voltage drop characteristics

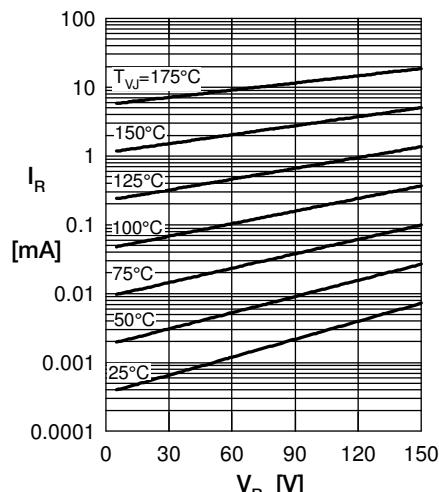


Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

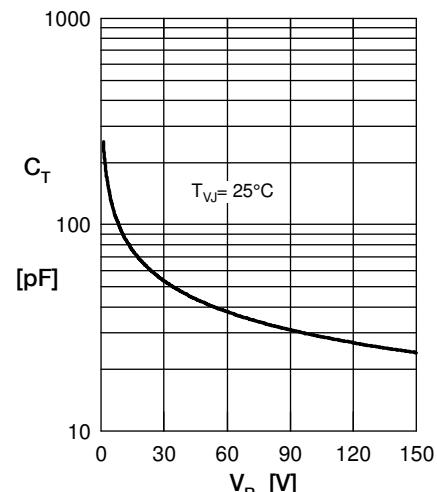


Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

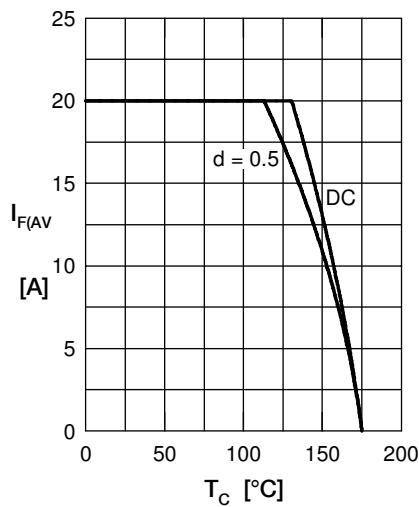


Fig. 4 Average forward current $I_{F(AV)}$ vs. case temp. T_C

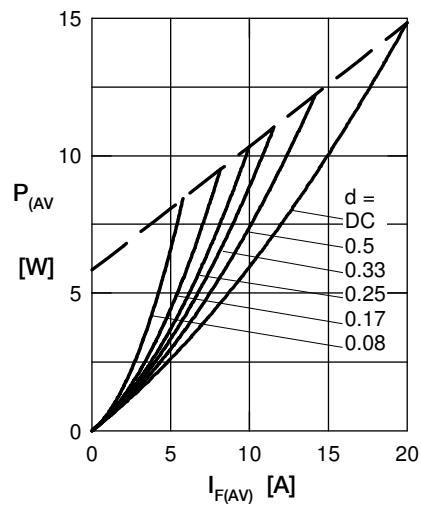
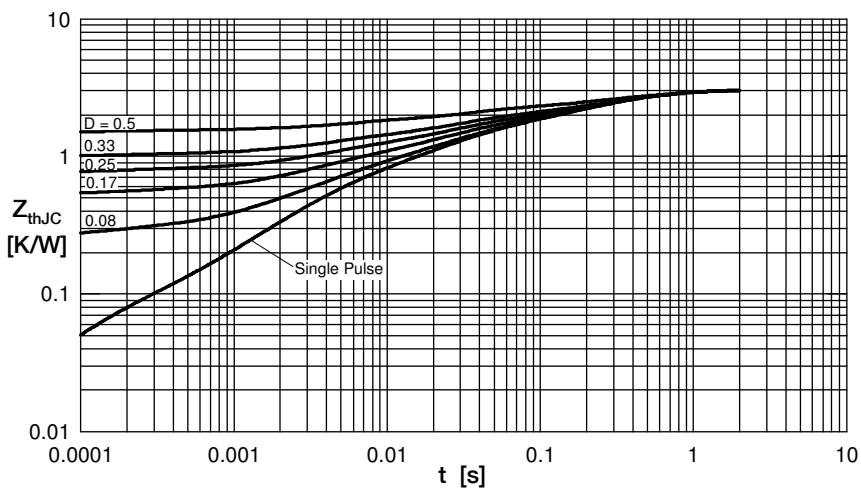


Fig. 5 Forward power loss characteristics



Note: All curves are per diode

Fig. 6 Transient thermal impedance junction to case at various duty cycles